



FW811 — N-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- 4V drive.
- Composite type, facilitating high-density mounting.

Specifications

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		35	V
Gate-to-Source Voltage	V_{GSS}		± 20	V
Drain Current (DC)	I_D		8	A
Drain Current ($PW \leq 10s$)	I_D	Duty cycle $\leq 1\%$	9	A
Drain Current ($PW \leq 10\mu s$)	I_{DP}	Duty cycle $\leq 1\%$	52	A
Allowable Power Dissipation	P_D	When mounted on ceramic substrate (2000mm ² ×0.8mm) 1unit, $PW \leq 10s$	2.0	W
Total Dissipation	P_T	When mounted on ceramic substrate (2000mm ² ×0.8mm), $PW \leq 10s$	2.2	W
Channel Temperature	T_{ch}		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1\text{mA}$, $V_{GS}=0\text{V}$	35			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=35\text{V}$, $V_{GS}=0\text{V}$			1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 16\text{V}$, $V_{DS}=0\text{V}$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10\text{V}$, $I_D=1\text{mA}$	1.2		2.6	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10\text{V}$, $I_D=8\text{A}$	2.7	4.5		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=8\text{A}$, $V_{GS}=10\text{V}$		18	24	$\text{m}\Omega$
	$R_{DS(on)2}$	$I_D=4\text{A}$, $V_{GS}=4.5\text{V}$		29	41	$\text{m}\Omega$
	$R_{DS(on)3}$	$I_D=4\text{A}$, $V_{GS}=4\text{V}$		39	55	$\text{m}\Omega$

Marking : W811

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FW811

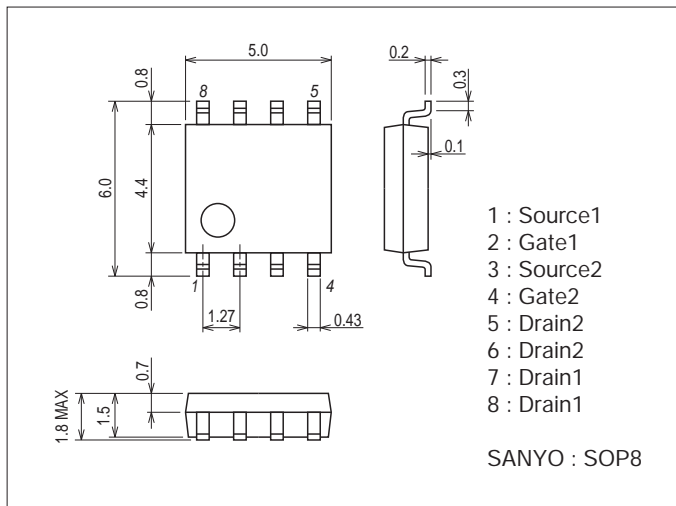
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V _{DS} =20V, f=1MHz		660		pF
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		90		pF
Reverse Transfer Capacitance	Crss	V _{DS} =20V, f=1MHz		60		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		10		ns
Rise Time	t _r	See specified Test Circuit.		50		ns
Turn-OFF Delay Time	t _{d(off)}	See specified Test Circuit.		40		ns
Fall Time	t _f	See specified Test Circuit.		40		ns
Total Gate Charge	Qg	V _{DS} =20V, V _{GS} =10V, I _D =8A		13.0		nC
Gate-to-Source Charge	Qgs	V _{DS} =20V, V _{GS} =10V, I _D =8A		2.4		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =20V, V _{GS} =10V, I _D =8A		3.2		nC
Diode Forward Voltage	V _{SD}	I _S =8A, V _{GS} =0V		0.81	1.2	V

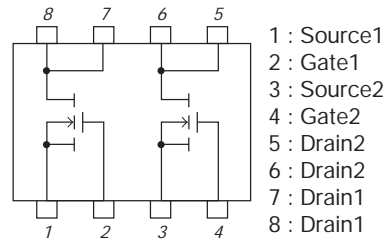
Package Dimensions

unit : mm (typ)

7005A-003

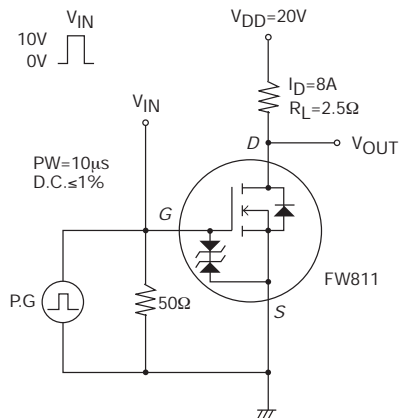


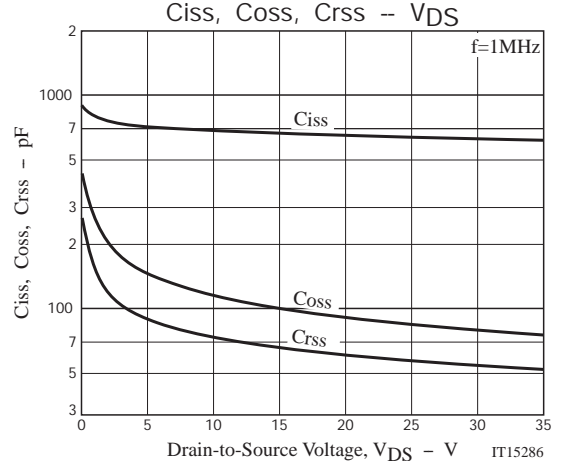
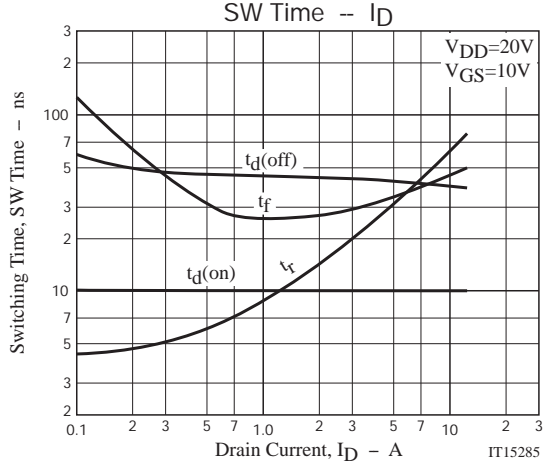
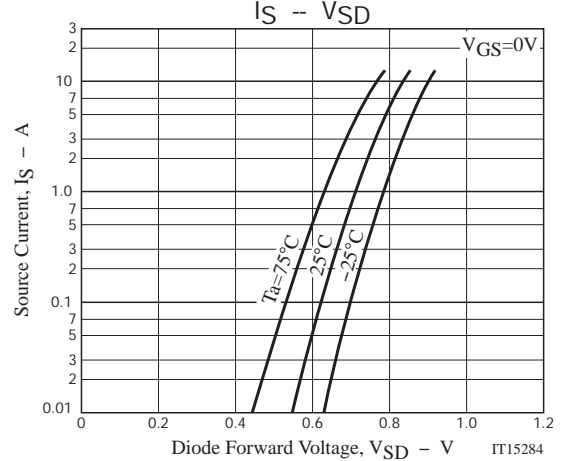
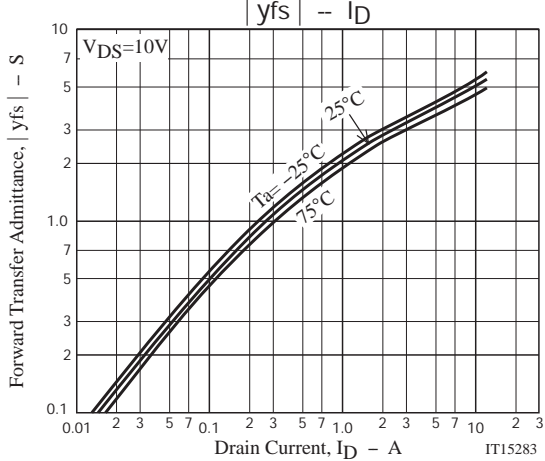
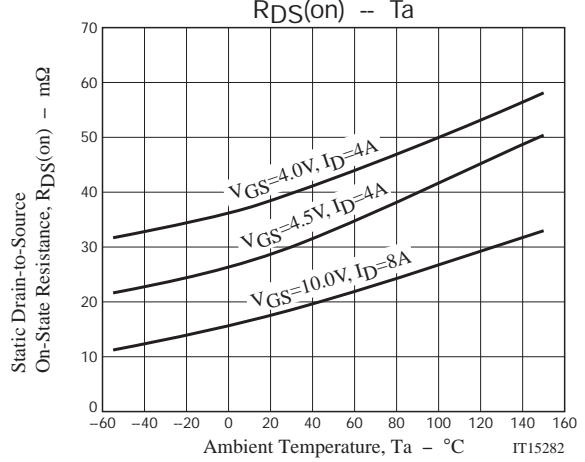
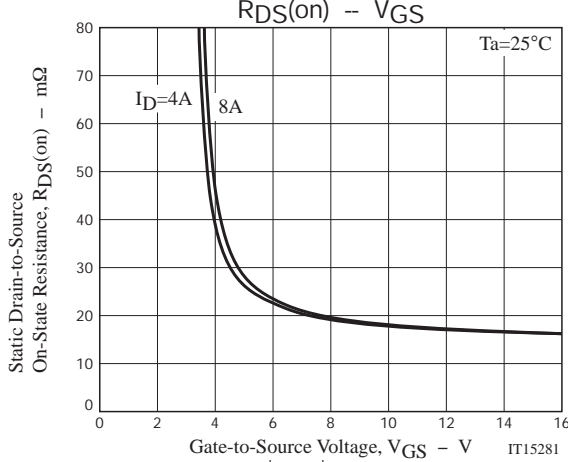
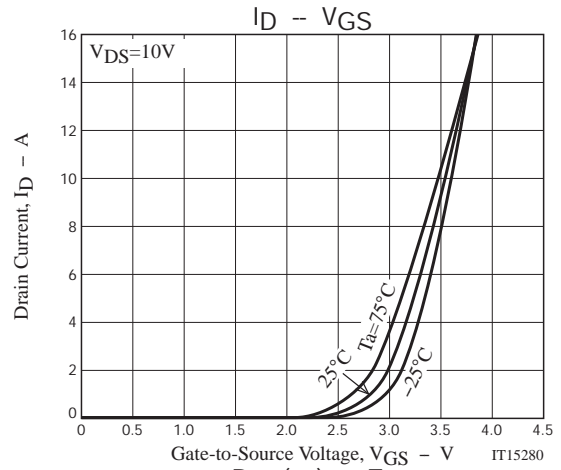
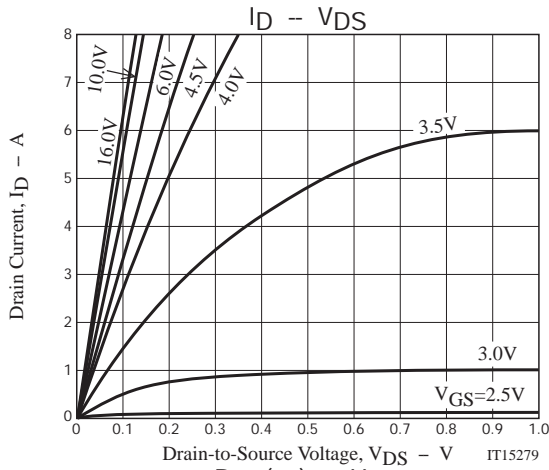
Electrical Connection

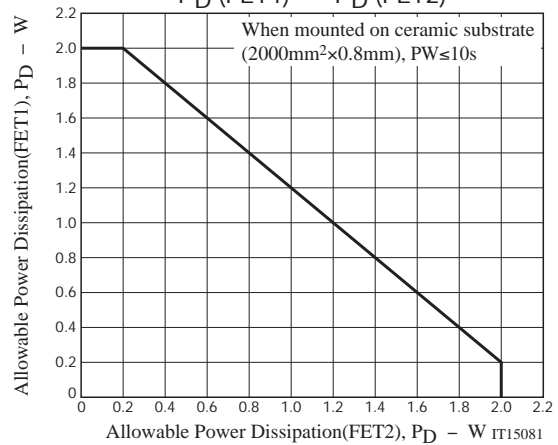
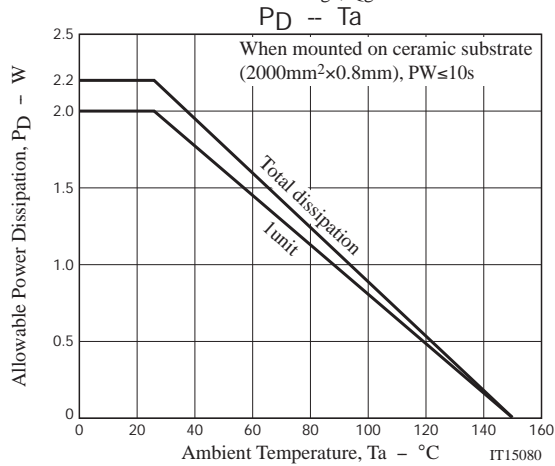
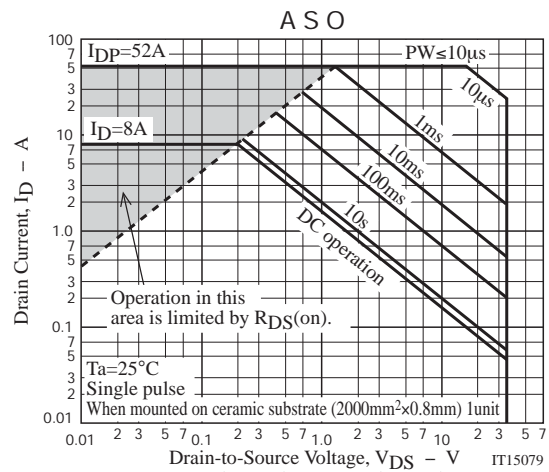
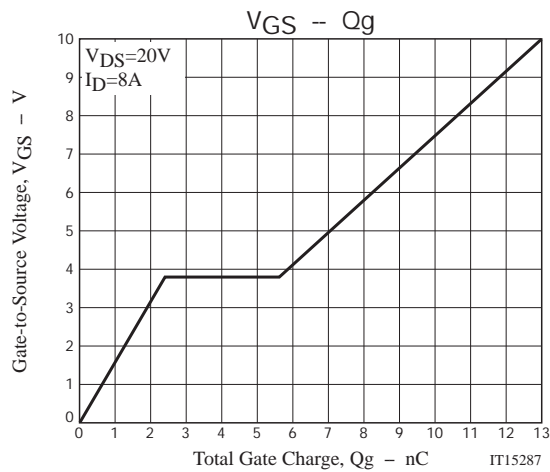


Top view

Switching Time Test Circuit







Note on usage : Since the FW811 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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